

isc N-Channel MOSFET Transistor

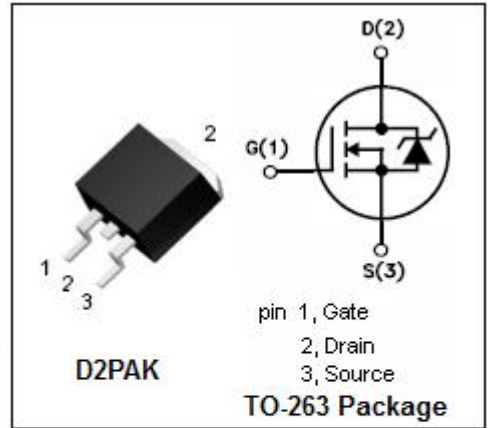
HUF75345S3ST

• DESCRIPTION

- Drain Current:  $I_D = 75A @ T_C = 25^\circ C$
- Drain Source Voltage :  $V_{DSS} = 55V(\text{Min})$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

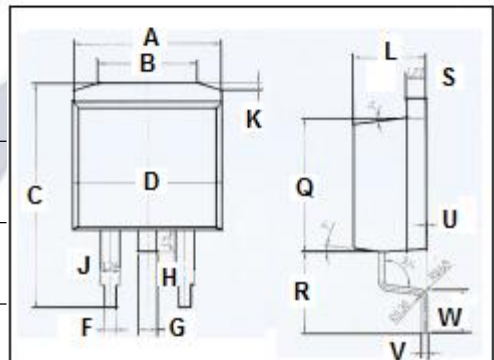
• APPLICATIONS

- Designed for high current, high speed switching, switch mode power supplies.



ABSOLUTE MAXIMUM RATINGS( $T_C = 25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS} = 0$ )	55	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $T_C = 25^\circ C$	75	A
$P_D$	Total Dissipation@ $T_C = 25^\circ C$	325	W
$T_j$	Max. Operating Junction Temperature	175	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~175	$^\circ C$



DIM	mm	
	MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.38	$^\circ C/W$

**isc N-Channel MOSFET Transistor****HUF75345S3ST**• ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 250μA	55			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =250μA	2.0		4.0	V
V <sub>SD</sub>	Diode Forward On-Voltage	I <sub>SD</sub> =75A ;V <sub>GS</sub> = 0			1.25	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =75A			10	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 50V; V <sub>GS</sub> = 0			1	μA
		V <sub>DS</sub> = 40V; V <sub>GS</sub> = 0			250	